

| Number | Hits | Search Text | DB | Time stamp |
|--------|------|---|---|-----------------|
| 9 | 5 | (ingan gainn) adj channel) | USPAT; US-PCPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/11/11 1:44 |
| 10 | 19 | (ingan gainn (indium adj gallium adj nitride) adj channel) | USPAT; US-PCPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/11/11 1:44 |
| 11 | 36 | hemt (high adj electron adj mobility adj transistor)) and (gan (gallium adj nitride)) and relax\$4 | USPAT; US-PCPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/11/11 1:44 |
| 12 | 18 | (hemt (high adj electron adj mobility adj transistor)) and (gan (gallium adj nitride)) and relax\$4) and (ingan gainn (indium adj gallium adj nitride)) | USPAT; US-PCPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/11/11 1:44 |

| Line Number | Hits | Search Text | IB | Time Stamp |
|-------------|------|--|---|------------------|
| 10 | 0 | ((ingan gainn) near5 channel) and (partial\$2 adj relaxed) | USPAT; US-PPHUB; EPO; JPO; DERWENT; IBM TDB | 2003/07/15 11:07 |
| 11 | 0 | (hemt (high adj electron adj mobility adj transistor)) and ((partial near5 relaxed adj channel) | USPAT; US-PPHUB; EPO; JPO; DERWENT; IBM TDB | 2003/07/15 11:07 |
| 12 | 0 | (hemt (high adj electron adj mobility adj transistor) and third near5 channel) and @ayk2000 and (ingaas gainn) and ((partial\$2 adj relaxed) near5 channel) | USPAT; US-PPHUB; EPO; JPO; DERWENT; IBM TDB | 2003/07/15 11:07 |
| 13 | 0 | ((partial\$2 adj relaxed) near5 channel) and (ingan gainn) | USPAT; US-PPHUB; EPO; JPO; DERWENT; IBM TDB | 2003/07/15 11:07 |
| 14 | 17 | ((ingan gainn) near5 channel) | USPAT; US-PPHUB; EPO; JPO; DERWENT; IBM TDB | 2003/07/15 11:07 |
| 15 | 3 | (hemt (high adj electron adj mobility adj transistor)) and ((ingan gainn) near5 channel) | USPAT; US-PPHUB; EPO; JPO; DERWENT; IBM TDB | 2003/07/15 11:07 |